# 2SA2075

## Silicon PNP epitaxial planar type

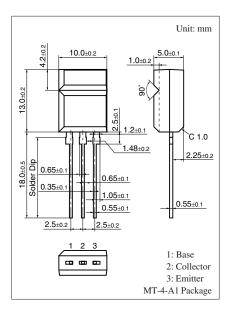
Power supply for Audio & Visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

#### ■ Features

- ullet High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- $\bullet$  Superior forward current transfer ratio  $h_{\text{FE}}$  linearity
- Allowing supply with the radial taping (MT-4)

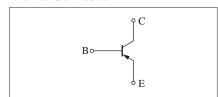
### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)		V <sub>CBO</sub>	-80	V
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	-80	V
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	-6	V
Collector current		$I_C$	-3	A
Peak collector current	$I_{CP}$	-5	A	
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	15	W
dissipation	$T_a = 25^{\circ}C$		2.0	
Junction temperature		$T_{j}$	150	°C
Storage temperature		$T_{stg}$	-55 to +150	°C



Marking Symbol: A2075

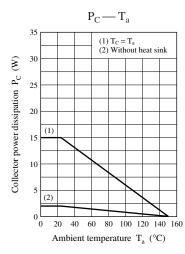
#### Internal Connection

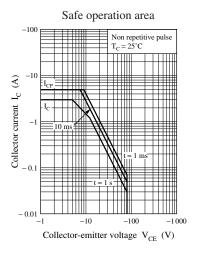


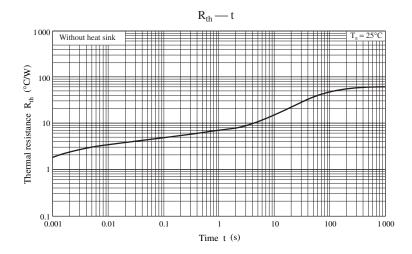
### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -10 \text{ mA}, I_B = 0$	-80			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -80 \text{ V}, I_E = 0$			-100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -80 \text{ V}, I_{B} = 0$			-100	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	80		250	
	h <sub>FE2</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -3 \text{ A}, I_B = -375 \text{ mA}$			-1.0	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = -0.1 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Turn-on time	t <sub>on</sub>	$I_C = -1$ A, Resistance loaded		0.2		μs
Storage time	t <sub>stg</sub>	$I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A}$		0.7		μs
Fall time	t <sub>f</sub>	$V_{CC} = -50 \text{ V}$		0.1		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.







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